

L Number	Hits	S arch Text	DB	Time stamp
1	751	((Core and clad\$4)) and wave\$guide and (mask or hard4mask r etch\$ mask)) and (resist r ph t resist)	USPAT; US-PGPUB; DERWENT	2003/02/12 08:53
3	164	((Core and clad\$4)) and wave\$guide and (mask or hard4mask or etch\$ mask)) and (resist or photoresist)) and (Cr or chrome or chromium)	USPAT; US-PGPUB; DERWENT	2003/02/12 11:08
5	451	((Core and clad\$4)) and wave\$guide and (mask or hard4mask or etch\$ mask)) and (resist or photoresist)) and \$4align\$4	USPAT; US-PGPUB; DERWENT	2003/02/12 10:35
7	97	((Core and clad\$4)) and wave\$guide and (mask or hard4mask or etch\$ mask)) and (resist or photoresist)) and (Cr or chrome or chromium)) and (align\$3 or self\$align\$3)	USPAT; US-PGPUB; DERWENT	2003/02/12 11:09
8	95	((Core and clad\$4)) and wave\$guide and (mask or hard4mask or etch\$ mask)) and (resist or photoresist)) and (Cr or chrome or chromium)) and (align\$3 or self\$align\$3)) and (quartz or silica or SiO2 or Glass)	USPAT; US-PGPUB; DERWENT	2003/02/12 11:10
-	989	(430/321).CCLS.	USPAT; US-PGPUB; DERWENT	2003/02/10 11:31
-	143	(216/25,26).CCLS.	USPAT; US-PGPUB; DERWENT	2003/02/10 15:12
-	882	Wave\$guide and micro\$machin\$4	USPAT; US-PGPUB; DERWENT	2003/02/10 15:30
-	580	(Wave\$guide and micro\$machin\$4) and etch\$4	USPAT; US-PGPUB; DERWENT	2003/02/10 15:15
-	35	(Wave\$guide and micro\$machin\$4).clm.	USPAT; US-PGPUB; DERWENT	2003/02/10 16:52
-	49	(Wave\$guide and micro\$machin\$4) and self\$align\$3	USPAT; US-PGPUB; DERWENT	2003/02/10 15:30
-	218	(Wave\$guide and micro\$machin\$4) and ((Core and clad\$4))	USPAT; US-PGPUB; DERWENT	2003/02/10 16:43
-	125	(65/385).CCLS.	USPAT; US-PGPUB; DERWENT	2003/02/10 16:50
-	101	(65/429).CCLS.	USPAT; US-PGPUB; DERWENT	2003/02/10 17:40
-	1095	(385/88).CCLS.	USPAT; US-PGPUB; DERWENT	2003/02/10 16:52
-	19	(Wav \$guide and micr \$machin\$4) and ((385/88).CCLS.)	USPAT; US-PGPUB; DERWENT	2003/02/10 16:59

-	754	(385/129).CCLS.	USPAT; US-PGPUB; DERWENT	2003/02/10 16:59
-	19	(Wave\$guid and micr \$machin\$4) and ((385/129).CCLS.)	USPAT; US-PGPUB; DERWENT	2003/02/10 17:02
-	926	(385/147).CCLS.	USPAT; US-PGPUB; DERWENT	2003/02/10 17:02
-	4	(Wave\$guide and micro\$machin\$4) and ((385/147).CCLS.)	USPAT; US-PGPUB; DERWENT	2003/02/10 17:02
-	250	((Core and clad\$4)) and ((385/88).CCLS.)	USPAT; US-PGPUB; DERWENT	2003/02/10 17:41
-	27947	(Core and clad\$4)	USPAT; US-PGPUB; DERWENT	2003/02/11 18:06
-	67672	wave\$guide	USPAT; US-PGPUB; DERWENT	2003/02/11 18:07
-	464166	mask or hard4mask or etch\$ mask	USPAT; US-PGPUB; DERWENT	2003/02/11 18:08
-	3007	((Core and clad\$4)) and wave\$guide and (mask or hard4mask or etch\$ mask)	USPAT; US-PGPUB; DERWENT	2003/02/11 18:09
-	310275	resist or photoresist	USPAT; US-PGPUB; DERWENT	2003/02/11 18:10